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12/31/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of )  
Shunpei YAMAZAKI et al. )  
Serial No. 08/691,434 )  
Filed: August 2, 1996 )  
For: METHOD OF FABRICATING )  
SEMICONDUCTOR DEVICES AND )  
APPARATUS FOR PROCESSING A )  
SEMICONDUCTOR )

Art Unit: 2822  
Examiner: M. Wilczewski

**CERTIFICATE OF MAILING**

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Washington, D.C. 20231, on 12/13/02

**PRELIMINARY AMENDMENT**

Honorable Commissioner of Patents  
Washington, D.C. 20231

Sir:

In response to the Office Action dated August 13, 2002 please amend the above-  
identified application as follows:

**IN THE CLAIMS:**

Please cancel claims 76-77, 79, 84-85 and 90-91 and amend claims 16, 56, and 74-  
75 as follows:

16. (Amended) An apparatus for processing a semiconductor comprising:
- a first vacuum chamber;
  - an ion introducing apparatus for doping a semiconductor layer formed over a substrate with a dopant impurity through an insulating film comprising oxide provided over said semiconductor layer;
  - an etching apparatus for etching said insulating film comprising oxide to expose a surface of said semiconductor layer, said etching apparatus connected to said ion introducing apparatus through said first vacuum chamber;

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